

Vážené kolegyne a kolegovia, pozývame vás na seminár:

Dr. Ievgen Brytavskiy
Odessa I.I. Mechnikov National University
Odessa, Ukraine

Technology and characterization of advanced devices based on III-V semiconductors

Abstract: I will present the results of my 6-month research stay at IEE in the frame of SAIA NSP scholarship. Seminar will be devoted to research of MOS transistors with HfO₂ gate oxide and epitaxial lift-off of thin GaAs films. Transistor technology and characterization, technological control of electrical properties of D-mode and E-mode Metal-Oxide-Semiconductor transistors, investigation of the epitaxial lift-off technique for GaAs/AlAs layer structures for flexible electronics applications will be discussed. Also the results of ALD and MOCVD coverage of porous silicon by ruthenium oxide for photocatalysis applications will be presented.

Seminár sa uskutoční v piatok 24.3.2017 o 10.00 v zasadačke EIÚ SAV.